Ethylenediamine organic chemical detection by field-effect transistor sensors fabricated with Bismuth-Vanadium Oxide-Tungsten Oxide  $(Bi(V_2O_4)-WO_2)$  nanosheets

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This work reports the preparation of bismuth-vanadium oxide-tungsten oxide  $Bi(V_2O_4)-WO_2$ nanosheets (NSs) via hydrothermal method at low temperature and utilized as the electrochemical electrode for fabricating field-effect transistor (FETs) based sensor. Synthesized  $Bi(V_2O_4)-WO_2$ displayed defined and thin sheet like morphology with the average thickness of ~35 nm. The synthesized  $Bi(V_2O_4)-WO_2$  NSs fabricated FET sensor was benefited by the large surface area, resulted in the fast detection of ethylenediamine chemical at very low concentration. The sensing results displayed a reproducible sensitivity of ~13.27 mAmM<sup>-1</sup>cm<sup>-2</sup>, detection limit of ~72.15 nM with the correlation coefficient (R) of ~0.99644 and good linearity from 10 mM to 100 mM. The fabricated  $Bi(V_2O_4)-WO_2$  NSs FETs sensor exhibited reproducibile and excellent stability of sensing performance and thus, confirmed it as useful tool for water maintaining system.